# XP0111H

### Silicon PNP epitaxial planar type

For digital circuits

#### Features

- Two elements incorporated into one package (Emitter-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

#### Basic Part Number

• UNR211H  $\times$  2

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

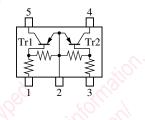
Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-50	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V	
Collector current	I <sub>C</sub>	-100	mA	
Total power dissipation	P <sub>T</sub>	150	mW	
Junction temperature	Тј	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

### Package

- Code
- SMini5-G1
- Pin Name
  1: Base (Tr1)
- 2: Emitter
- 3: Base (Tr2)
- 4: Collector (Tr2)
- 5: Collector (Tr1)

Marking Symbol: 9X

Internal Connection



#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

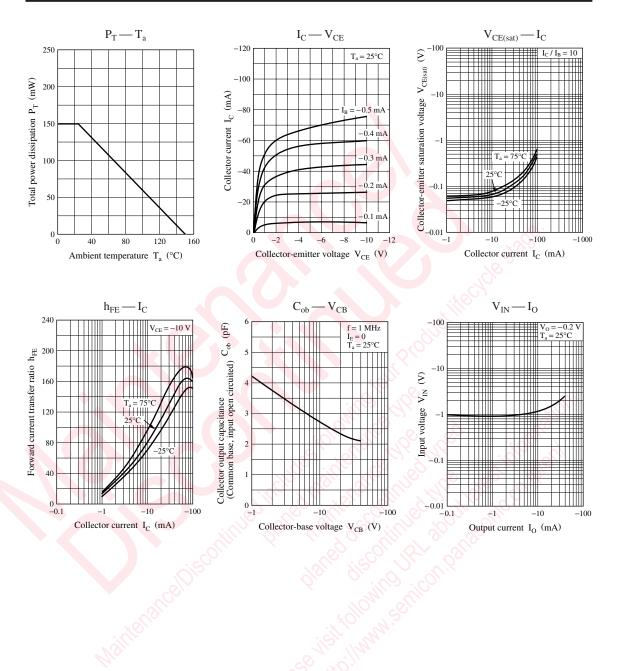
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10 \ \mu \text{A}, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -50 \text{ V}, I_B = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = -6 V, I_C = 0$			- 0.5	mA
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	30			_
h <sub>FE</sub> Ratio *	h <sub>FE(Small</sub>	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	0.50	0.99		
	/Large)					
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.3 \text{ mA}$			- 0.25	V
Output voltage high-level	V <sub>OH</sub>	$V_{CC} {=} -5  V,  V_B {=} -0.5  V,  R_L {=} 1  k\Omega$	-4.9			V
Output voltage low-level	V <sub>OL</sub>	$V_{CC} = -5 \text{ V}, \text{ V}_{B} = -2.5 \text{ V}, \text{ R}_{L} = 1 \text{ k}\Omega$			- 0.2	V
Input resistance	R <sub>1</sub>		-30%	2.2	+30%	kΩ
Resistance ratio	R <sub>1</sub> / R <sub>2</sub>		0.17	0.22	0.27	
Transition frequency	f <sub>T</sub>	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. \*: Ratio between 2 elements

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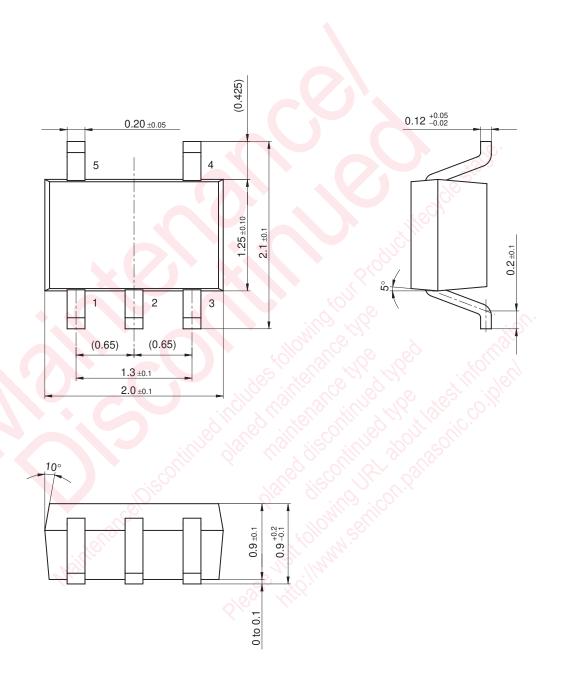




### Panasonic

### SMini5-G1

Unit: mm



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